

## FEATURES

**n HIGH POWER**

P1dB=45.0dBm at 14.0GHz to 14.5GHz

**n HIGH GAIN**

G1dB=5.5dB at 14.0GHz to 14.5GHz

**n LOW INTERMODULATION DISTORTION**

IM3(Min.)=-25dBc at Po=38.0dBm Single Carrier Level

**n BROAD BAND INTERNALLY MATCHED FET**

**n HERMETICALLY SEALED PACKAGE**

## RF PERFORMANCE SPECIFICATIONS ( Ta= 25°C )

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset≒7.0A f = 14.0 to 14.5GHz	dBm	44.0	45.0	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	4.5	5.5	—
Drain Current	IDS1		A	—	10.0	11.0
Power Added Efficiency	ηadd		%	—	23	—
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 38.0dBm	dBc	-25	—	—
Drain Current	IDS2	(Single Carrier Level)	A	—	9.0	10.1
Channel Temperature Rise	ΔTch	(VDS X IDS +Pin-P1dB) X Rth(c-c)	°C	—	—	100

**Recommended gate resistance(Rg) : Rg= 28 W(MAX.)**

## ELECTRICAL CHARACTERISTICS ( Ta= 25°C )

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 9.6A	S	—	5.5	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 290mA	V	-0.7	-2.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	20.0	—
Gate-Source Breakdown Voltage	VGSO	IGS= -290μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	—	1.1

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